SL3ICS3001

UCODE HSL bumped wafer specification

Rev. 3.0 — 6 July 2009 070730 Product data sheet addendum PUBLIC

1. General description

The SL3ICS3001FW is a contactless tag IC designed for tags and labels for RFID and AIDC system applications.

This specification describes electrical, physical and dimensional properties of Au-bumped, sawn wafers on FFC.

Functionality of the integrated circuit are described in <u>Ref. 2 "Data sheet - SL3ICS3001</u> UCODE HSL, document number: 0728**".

2. Ordering information

Table 1. Ordering in	formation		
Type number	Package		Version
	Name	Description	
SL3ICS3001FW/V1	Wafer	Bumped, sawn wafer on FCC, 150 $\mu m,$ inked	-

3. Mechanical specification

3.1 Wafer

Designation:	each wafer is scribed with batch number and wafer number
Diameter:	200 mm (8")
Thickness:	150 μm ± 15 μm
 Bond pad location: 	see Figure 1 "Bondpad plan SL3ICS3001"
Electrical connection substrate:	RFN
Orientation of dies relative to notch: <u>locations SL3ICS3001</u> "	see Figure 2 "Chip orientation and bondpad
Process:	C075EE
Batch size:	24 wafers
Minimum average yield per batch:	30 %



3.2 Wafer backside

- Material:
- Treatment:
- Roughness:

3.3 Chip dimensions

- Die size without scribe:
- Die size with scribe:
- Scribe lines: ٠

Si ground and stress release R_a max. 0.5 μ m, R_t max. 5 μ m

500 nm / 600 nm

35 - 80 HV 0.005

> 70 MPa

18 µm

± 3 μm

±4 μm

± 5 μm

± 1.5 μm

60 x 60 µm (pad RFN is connected to

60 x 60 µm (pads TP1 and TP2 are disconnected when the wafer is sawn)

substrate and ground)

 $0.91 \text{ mm x} 0.84 \text{ mm} = 0.76 \text{ mm}^2$ $0.99 \text{ mm x} 0.92 \text{ mm} = 0.91 \text{ mm}^2$ x-line: 86.4 µm (scribe line width is measured on top metal layer) y-line: 86.4 µm (scribe line width is measured on top metal layer)

3.4 Passivation on front

•	Туре:	sandwich structure
•	Material:	PSG / Nitride (on top)

Thickness: •

3.5 Au bump

Bump material:	> 99.9% pure Au

- Bump hardness:
- Bump shear strength:
- · Bump height:
- Bump height uniformity:
 - within a die: $\pm 2 \mu m$
 - within a wafer:
 - wafer to wafer:
- Bump flatness:
- Bump size:
 - RFP, RFN
 - TP1, TP2
- · Bump size variation:
- Under bump metallization: sputtered TiW

3.6 Fail die identification

All fail dies are inked according to electrical test results.

Electronic wafer mapping covers the electrical test results and additionally the results of mechanical/visual inspection.

For details please refer to <u>Ref. 1 "Data sheet - General specification for 8" wafer on</u> <u>UV-tape, document number: 1005**"</u>.

4. Limiting values

Table 2. Limiting values^{[1][2]}

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I _{IN}	input current		-	±10	mA
T _{stg}	storage temperature bare die		-55	+125	°C
P _{tot}	power dissipation		-	30	mW
T _{amb}	operating temperature		-40	+85	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model	[3] _	±1	kV

 Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any conditions other than those described in the Operating Conditions and Electrical Characteristics section of this specification is not implied.

[2] This product includes circuitry specifically designed for the protection of its internal devices from the damaging effects of excessive static charge. Nonetheless, it is suggested that conventional precautions be taken to avoid applying greater than the rated maxima.

[3] For ESD measurement, the die chip has been mounted into a CDIP8 package.

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5. Characteristics

5.1 DC characteristics

This section provides additional information to the data sheet (<u>Ref. 2</u>) and overrules the data sheet in case of a conflict.

Table 3.Electrical characteristics $T_{eq} = -25$ to $85 \, \text{C}$

amb2	T _{amb} = -23 10 65 C						
Symbol	Parameter	Conditions		Min	Max	Unit	
$V_{\text{RFP,min}}$	minimum supply voltage for communcation		<u>[1]</u>	1.15	1.55	V	
V _{RFP,write}	minimum supply voltage for EEPROM programming		<u>[1]</u>	2.10	2.40	V	
I _{RFP,typ}	chip current	V _{RFP} = 1.9 V		-	17	μA	
R_{Mod}	chip input resistance	modulator turned on; I _{RFP} = 10 mA		-	180	Ω	
EEPROM	characteristics						
t _{ret}	retention time	$T_{amb} \le 55 \ ^{\circ}C$		10	-	year	
N _{endu(W)}	write endurance	$T_{amb} = 22 \ ^{\circ}C$		100000	-	cycle	

[1] The measured operating voltage is the open-circuit voltage of a source with a 50 Ω output impedance.

5.2 AC characteristics

This section provides additional information to the data sheet (<u>Ref. 2</u>) and overrules the data sheet in case of a conflict.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Z ₈₆₇	input impedance	T = 22 °C, f = 867 MHz	<u>[1]</u>	-	41 - j865	-	Ω
Z ₉₁₅		T = 22 °C, f = 915 MHz	<u>[1]</u>	-	34.5 - j815	-	Ω
Z ₂₄₅₀		T = 22 °C, f = 2450 MHz	<u>[1]</u>	-	11.5 - j295	-	Ω
P ₈₆₇	minimum operating power	f = 869.5 MHz	[2]	-	-15	-	dBm
P ₉₁₅		f = 915 MHz	[2]	-	-14	-	dBm
P ₂₄₅₀	-	f = 2450 MHz	[2]	-	-9	-	dBm

[1] Measured at typcial "minimum operating power".

[2] Values apply for operation with low modulation index (18%) and high return datarate (4x forward link).

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6. Chip orientation and bond pad locations



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7. References

- [1] **Data sheet** *General specification for 8" wafer on UV-tape*, document number: 1005**1
- [2] Data sheet SL3/CS3001 UCODE HSL, document number: 0728**

8. Revision history

Table 5. R	evision history				
Document I	D Release date	Data sheet status	Change notice	Supersedes	
070730	20090706	Product data sheet addendum	-	070710	
Modifications	 The format of this d identity guidelines d 	ata sheet has been redesigned to of NXP Semiconductors.	o comply with the new		
	 Legal texts have be 	 Legal texts have been adapted to the new company name where appropriate. 			
	 Section 2 "Ordering 	information": updated			
	 Section 3 "Mechani 	cal specification": updated			
	Section 7 "Reference	<u>ces"</u> : updated			
070710	October 2003	Preliminary data sheet addendu	m	-	

^{1. ** ...} document version number

9. Legal information

9.1 Data sheet status

Product status ^[3]	Definition
Development	This document contains data from the objective specification for product development.
Qualification	This document contains data from the preliminary specification.
Production	This document contains the product specification.
	Product status ^[3] Development Qualification Production

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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